EMH2417R

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N-Channel Power MOSFET 12V, 11A, 10mΩ, Dual EMH8 Common Drain

Features

- Low On-resistance
- 2.5V drive
- Common-drain type
- Protection diode in

- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit		
Drain to Source Voltage	V _{DSS}		12	V		
Gate to Source Voltage	VGSS		±12	V		
Drain Current (DC)	ID		11	Α		
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40	Α		
Power Dissipation	PD	When mounted on ceramic substrate(900mm ² ×0.8mm) 1unit	1.3	W		
Total Dissipation	PT	When mounted on ceramic substrate(900mm ² ×0.8mm)	1.4	W		
Junction Temperature	Tj		150	°C		
Storage Temperature	Tstg		- 55 to +150	°C		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient	Post	96	°C /W
When mounted on ceramic substrate (900mm ² ×0.8mm)	$R_{\theta JA}$	90	C / W

Electrical Characteristics at Ta = 25°C

Davis and an		0 100	Value			
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	12			٧
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =10V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±1	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =6V, I _D =1mA	0.5		1.3	٧
Forward Transconductance	gFS .	V _{DS} =6V, I _D =5A		13		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =5A, V _{GS} =4.5V	6.4	8	10	mΩ
	R _{DS} (on)2	I _D =5A, V _{GS} =4.0V	6.8	8.5	11	mΩ
	R _{DS} (on)3	I _D =5A, V _{GS} =3.1V	8.8	11	15.4	mΩ
	R _{DS} (on)4	I _D =2.5A, V _{GS} =2.5V	11.2	14	19.6	mΩ

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ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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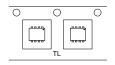
Dozometez	Councile of	Conditions	Value			11.2
Parameter	Symbol		min	typ	max	Unit
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		470		ns
Rise Time	t _r			1600		ns
Turn-OFF Delay Time	t _d (off)			8900		ns
Fall Time	tf			6400		ns
Total Gate Charge	Qg	V _{DS} =6V, V _{GS} =4.5V, I _D =11A		16		nC
Gate to Source Charge	Qgs			3		nC
Gate to Drain "Miller" Charge	Qgd			5		nC
Forward Diode Voltage	V _{SD}	I _S =11A, V _{GS} =0V		0.8	1.2	٧

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Ordering & Package Information

Device	Package	Shipping	note
EMH2417R-TL-H	EMH8	3,000 pcs. / reel	Pb-Free and Halogen Free

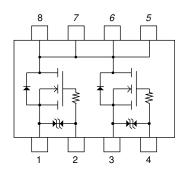
Packing Type:TL



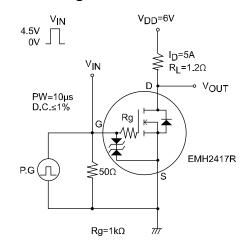
Marking

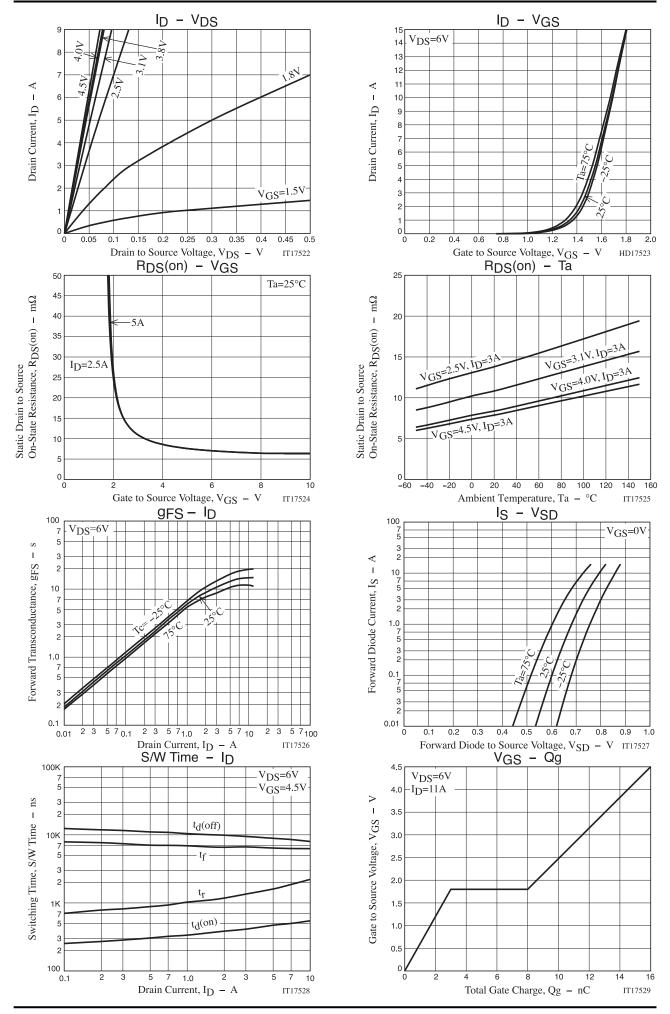


Electrical Connection

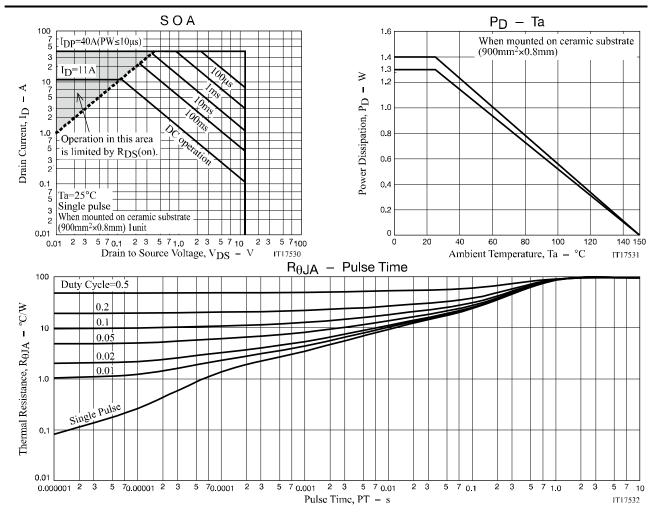


Switching Time Test Circuit





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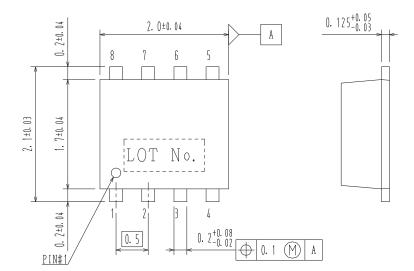
Package Dimensions

EMH2417R-TL-H

unit: mm

SOT-383FL / EMH8 CASE 419AT

ISSUE O



1: Source1

2: Gate1

3: Source2

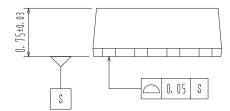
4 : Gate2

5: Drain

6: Drain

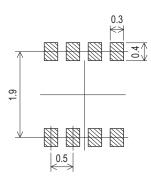
7 : Drain

8: Drain



0.05±0.05

Recommended Soldering Footprint



Note on usage: Since the EMH2417R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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